

FG4000GX-90DA

HIGH POWER INVERTER USE
PRESS PACK TYPE

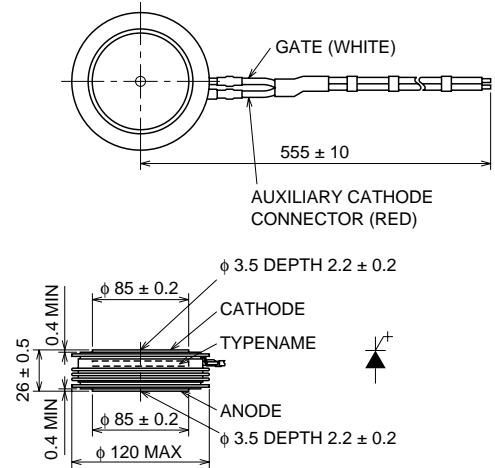
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- ITQRM Repetitive controllable on-state current 4000A
- IT(AV) Average on-state current 1200A
- VDRM Repetitive peak off state voltage 4500V
- Anode short type

OUTLINE DRAWING

Dimensions in mm



APPLICATION

Inverters, D.C. choppers, Induction heaters, D.C. to D.C. converters.

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		90DA		
VRRM	Repetitive peak reverse voltage	17		V
VRSM	Non-repetitive peak reverse voltage	17		V
VR(DC)	DC reverse voltage	17		V
VDRM	Repetitive peak off-state voltage*	4500		V
VDSM	Non-repetitive peak off-state voltage*	4500		V
VD(DC)	DC off-state voltage*	3600		V
VLTD5	Long term DC stability voltage*	3000		V

* : VGK = -2V

Symbol	Parameter	Conditions	Ratings	Unit
ITQRM	Repetitive controllable on-state current	V _{DM} = 4500V, T _J = 125°C, C _S = 4.0μF, L _S = 0.2μH	4000	A
IT(RMS)	RMS on-state current		1800	A
IT(AV)	Average on-state current	f = 60Hz, sine wave θ = 180°, T _r = 70°C	1200	A
ITSM	Surge (non-repetitive) on-state current	One half cycle at 60Hz	25	kA
I ² t	Current-squared, time integration	One cycle at 60Hz	2.6 × 10 ⁶	A ² s
diT/dt	Critical rate of rise of on-state current	V _D = 3400V, I _{GM} = 25A, T _J = 125°C	500	A/μs
VFGM	Peak forward gate voltage		10	V
VRGM	Peak reverse gate voltage		17	V
IFGM	Peak forward gate current		130	A
IRGM	Peak gate reverse current		900	A
PFGM	Peak forward gate power dissipation		520	W
PRGM	Peak reverse gate power dissipation		33	kW
PFG(AV)	Average forward gate power dissipation		130	W
PRG(AV)	Average reverse gate power dissipation		300	W
T _J	Junction temperature		-40 ~ +125	°C
T _{stg}	Storage temperature		-40 ~ +150	°C
—	Mounting force required	Recommended value 42	35 ~ 48	kN
—	Weight	Standard value	1220	g

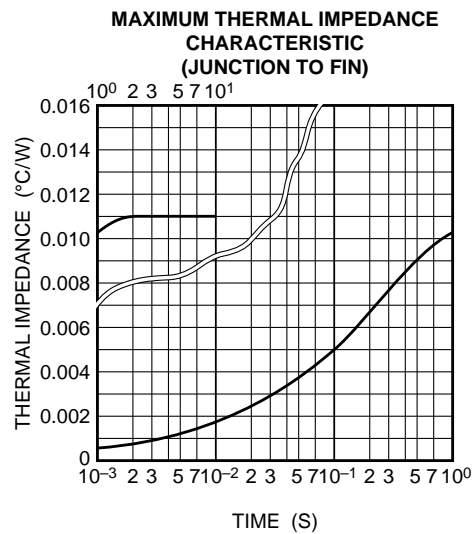
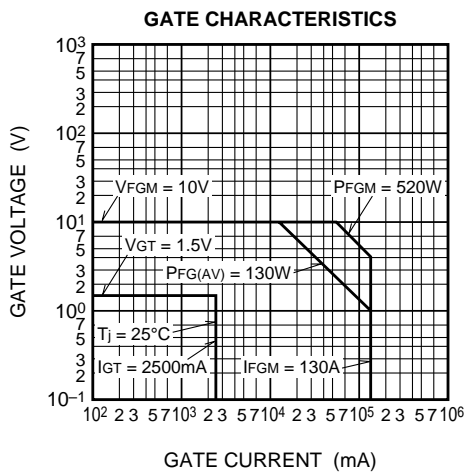
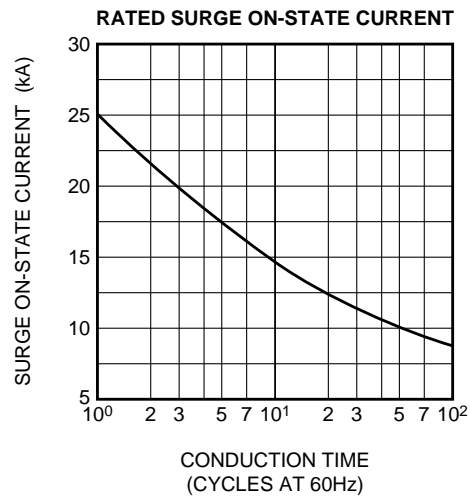
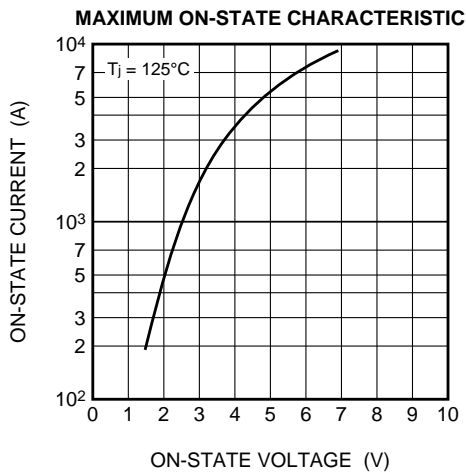
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ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{TM}	On-state voltage	T _j = 125°C, I _{TM} = 4000A, Instantaneous measurement	—	—	4.3	V
I _{RRM}	Repetitive peak reverse current	T _j = 125°C, V _{RRM} Applied	—	—	10	mA
I _{DRM}	Repetitive peak off-state current	T _j = 125°C, V _{DRM} Applied, V _{GK} = -2V	—	—	150	mA
I _{RG}	Reverse gate current	T _j = 125°C, V _{RG} = 17V	—	—	10	mA
dv/dt	Critical rate of rise of off-state voltage	T _j = 125°C, V _D = 2250V, V _{GK} = -2V	1000	—	—	V/μs
t _{gt}	Turn-on time	T _j = 125°C, I _{TM} = 4000A, I _{GM} = 25A, V _D = 3400V	—	—	8	μs
t _{gq}	Turn-off time	T _j = 125°C, I _{TM} = 4000A, V _{DM} = 4500V, diGQ/dt = -50A/μs V _{RG} = 17V, C _s = 4.0μF, L _s = 0.2μH	—	—	35	μs
I _{GQM}	Peak gate turn-off current		—	900	—	A
V _{GT}	Gate trigger voltage	DC METHOD : V _D = 24V, R _L = 0.1Ω, T _j = 25°C	—	—	1.5	V
I _{GT}	Gate trigger current		—	—	2500	mA
R _{th(j-f)}	Thermal resistance	Junction to fin	—	—	0.011	°C/W

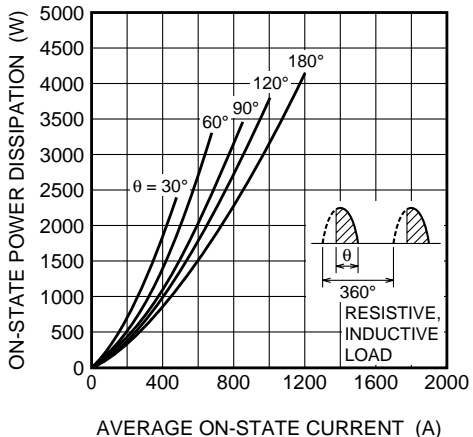
PERFORMANCE CURVES



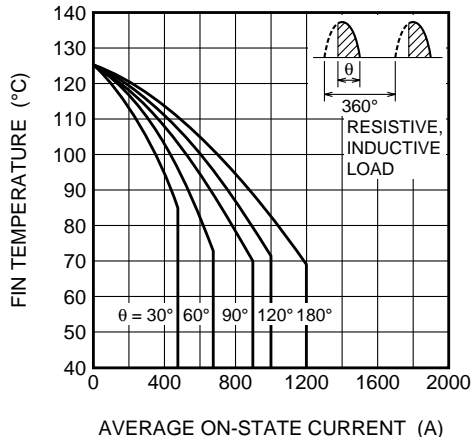
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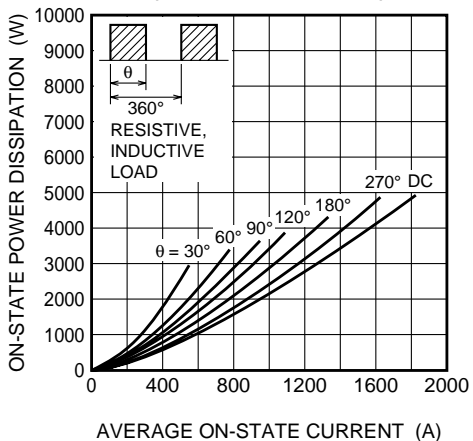
MAXIMUM ON-STATE POWER DISSIPATION CHARACTERISTICS (SINGLE-PHASE HALF WAVE)



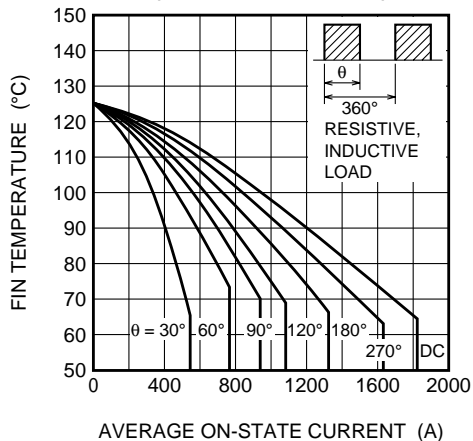
ALLOWABLE FIN TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)



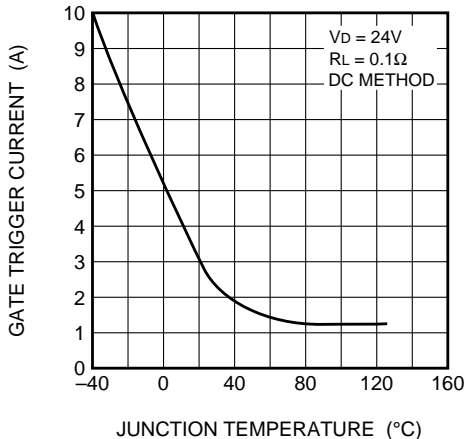
MAXIMUM ON-STATE POWER DISSIPATION CHARACTERISTICS (RECTANGULAR WAVE)



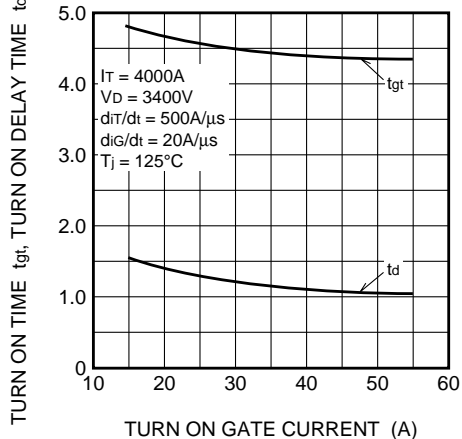
ALLOWABLE FIN TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)



GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE (MAXIMUM)

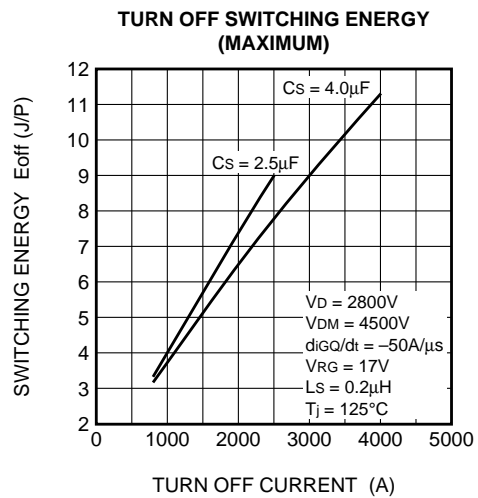
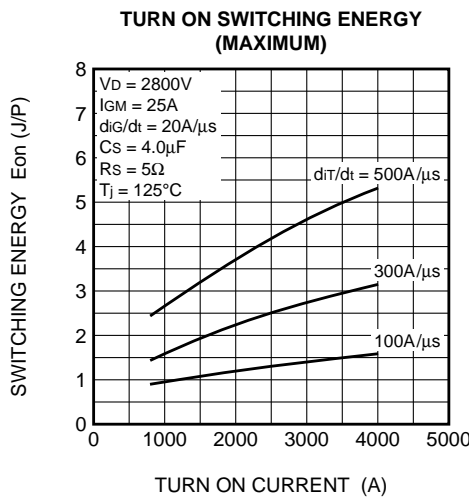
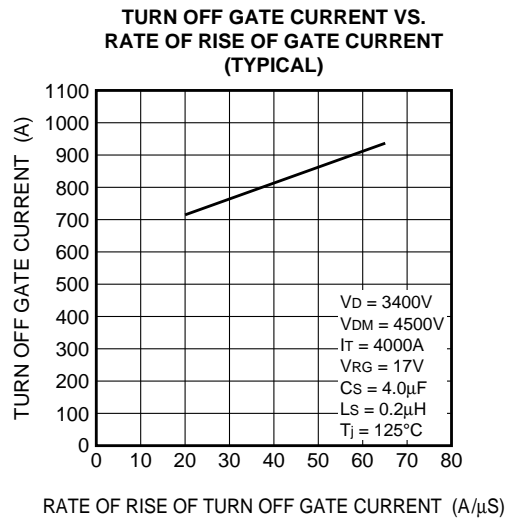
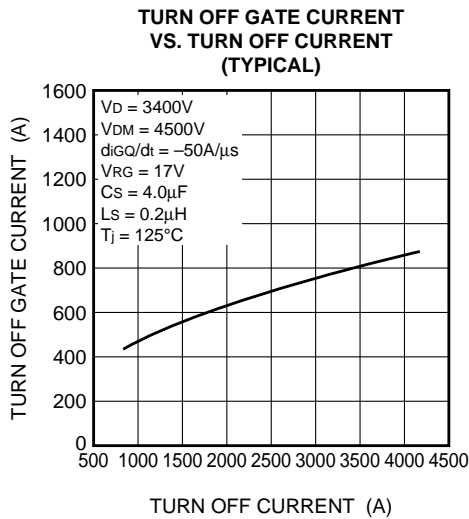
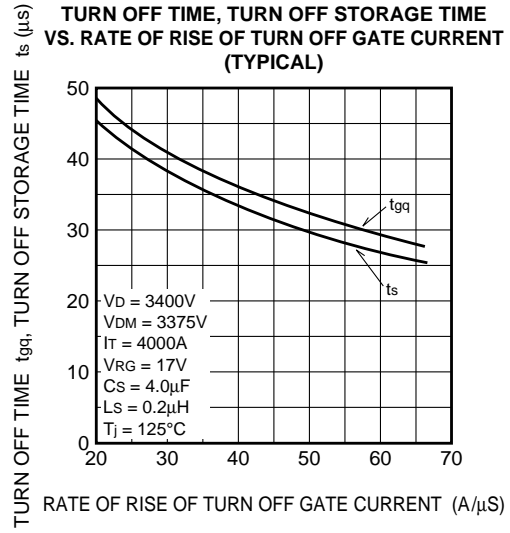
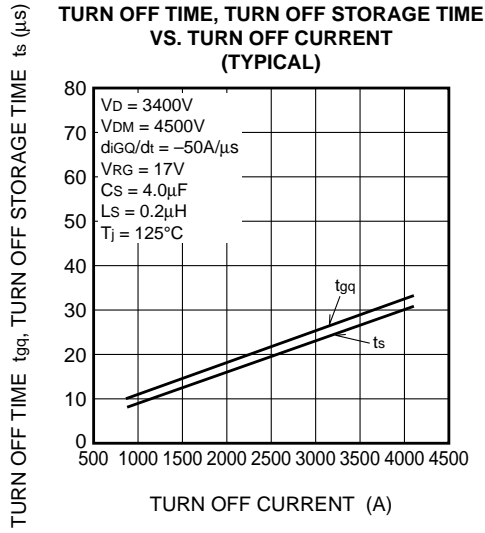


TURN ON TIME, TURN ON DELAY TIME VS. TURN ON GATE CURRENT (TYPICAL)



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Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Распределительные склады, находящиеся в России, Европе и в Китае, позволяют нам оперативно поставить необходимые компоненты в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям ISO 9001:2011

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